

## N-channel 200V 5.6mΩ Power MOSFET

### Description

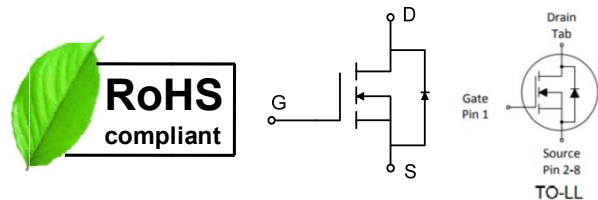
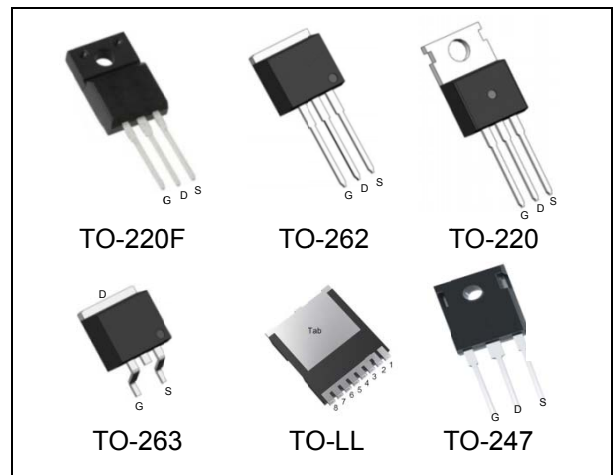
WMOS™ JN is suitable for applications which require superior power density and outstanding efficiency.

### Features

- Gate charge minimized
- Typ.  $R_{DS(on)} = 5.6m\Omega$
- 100% UIS tested
- Pb-free plating, Halogen free

### Applications

Switching applications



### Absolute Maximum Ratings

Parameter	Symbol	WMK/WMM/WMN/WMJ/WMLL	WML	Unit
Drain-source voltage	$V_{DSS}$	200		V
Continuous drain current <sup>1)</sup> ( $T_C = 25^\circ C$ )	$I_D$	145		A
( $T_C = 100^\circ C$ )		87		A
Pulsed drain current <sup>2)</sup>	$I_{DM}$	435		A
Gate-source voltage	$V_{GS}$	$\pm 20$		V
Avalanche energy, single pulse <sup>3)</sup>	$E_{AS}$	700		mJ
Avalanche energy, repetitive <sup>2)</sup>	$E_{AR}$	0.3		mJ
Avalanche current, repetitive <sup>2)</sup>	$I_{AR}$	5		A
Power dissipation ( $T_C = 25^\circ C$ )	$P_D$	312	35	W
- Derate above $25^\circ C$		2.5	0.28	W/ $^\circ C$
Operating and storage temperature range	$T_{j}, T_{stg}$	-55 to +150		$^\circ C$
Continuous diode forward current	$I_S$	145		A
Diode pulse current	$I_{S,pulse}$	435		A

### Thermal Characteristics

Parameter	Symbol	WMK/WMM/WMN/WMJ/WMLL	WML	Unit
Thermal resistance, junction-to-case	$R_{\theta JC}$	0.4	3.6	$^\circ C/W$
Thermal resistance, junction-to-ambient	$R_{\theta JA}$	62	80	$^\circ C/W$

**Electrical Characteristics**  $T_c = 25^\circ\text{C}$ , unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
<b>Static characteristics</b>						
Drain-source breakdown voltage	$BV_{DSS}$	$V_{GS}=0\text{ V}, I_D=1\text{ mA}$	200	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=0.25\text{mA}$	2.2	3.2	4.2	V
Drain cut-off current	$I_{DSS}$	$V_{DS}=200\text{ V}, V_{GS}=0\text{V},$ $T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	-	-	1	$\mu\text{A}$
Gate leakage current, forward	$I_{GSSF}$	$V_{GS}=20\text{V}, V_{DS}=0\text{V}$	-	-	500	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}, I_D=30\text{A}$ $T_j = 25^\circ\text{C}$	-	5.6	6.6	m $\Omega$
<b>Dynamic characteristics</b>						
Input capacitance	$C_{iss}$	$V_{DS}= 100\text{V}, V_{GS}= 0\text{V},$ $f = 1\text{ MHz}$	-	6788	-	pF
Output capacitance	$C_{oss}$		-	236	-	
Reverse transfer capacitance	$C_{rss}$		-	38	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 100\text{V}, I_D = 30\text{A}$ $R_G = 4.7\Omega, V_{GS}=10\text{V}$	-	16	-	ns
Rise time	$t_r$		-	31	-	
Turn-off delay time	$t_{d(off)}$		-	155	-	
Fall time	$t_f$		-	5	-	
<b>Gate charge characteristics</b>						
Gate to source charge	$Q_{gs}$	$V_{DD}=160\text{V}, I_D=30\text{A},$ $V_{GS}=0\text{ to }10\text{V}$	-	32	-	nC
Gate to drain charge	$Q_{gd}$		-	24	-	
Gate charge total	$Q_g$		-	121	-	
Gate plateau voltage	$V_{plateau}$		-	5.0	-	V
<b>Reverse diode characteristics</b>						
Diode forward voltage	$V_{SD}$	$V_{GS}=0\text{ V}, I_F=30\text{A}$	-	-	1.2	V
Reverse recovery time	$t_{rr}$	$V_R=50\text{V}, I_F=30\text{A},$ $di_F/dt=100\text{A}/\mu\text{s}$	-	160	-	ns
Reverse recovery charge	$Q_{rr}$		-	0.9	-	$\mu\text{C}$
Peak reverse recovery current	$I_{rrm}$		-	10	-	A

## Notes:

- Limited by  $T_{j\text{max}}$ . Maximum duty cycle  $D=0.5$ .
- Repetitive rating: pulse width limited by maximum junction temperature.
- $I_{AS} = 5\text{A}, V_{DD} = 50\text{V}, R_G = 25\Omega$ , starting  $T_j = 25^\circ\text{C}$ .

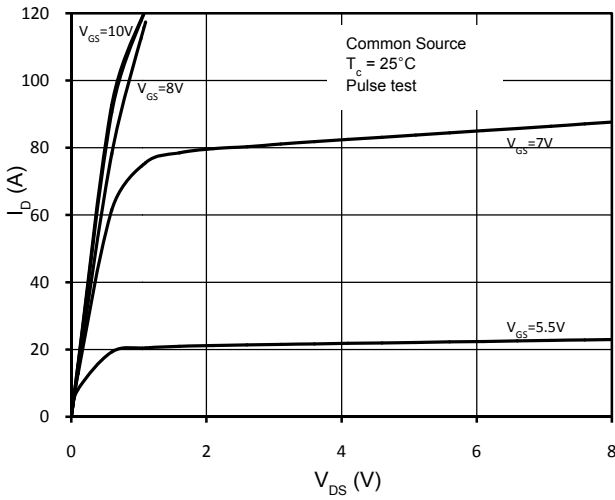


Figure 1. On-Region Characteristics

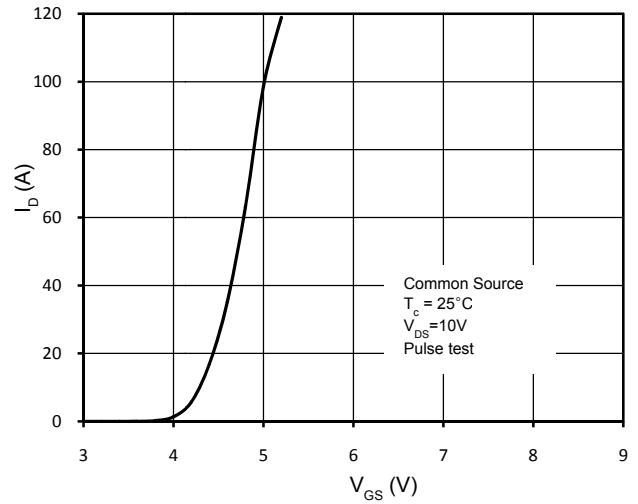


Figure 2. Transfer Characteristics

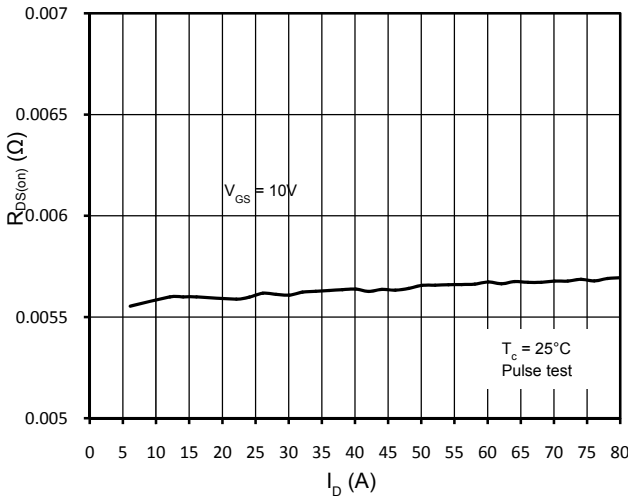


Figure 3. Static Drain-Source On Resistance

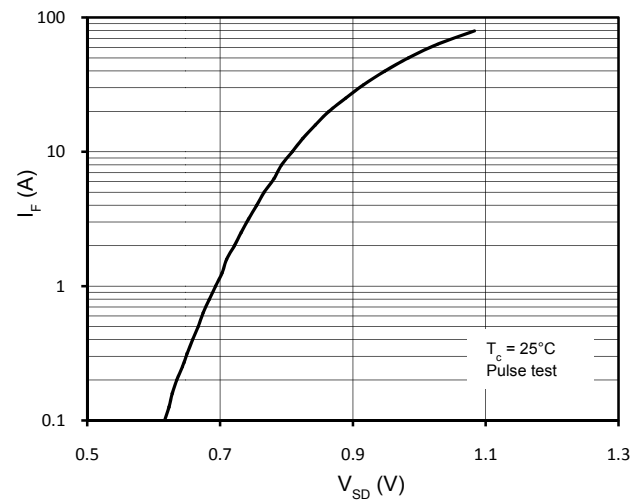


Figure 4. Body-Diode Forward Characteristics

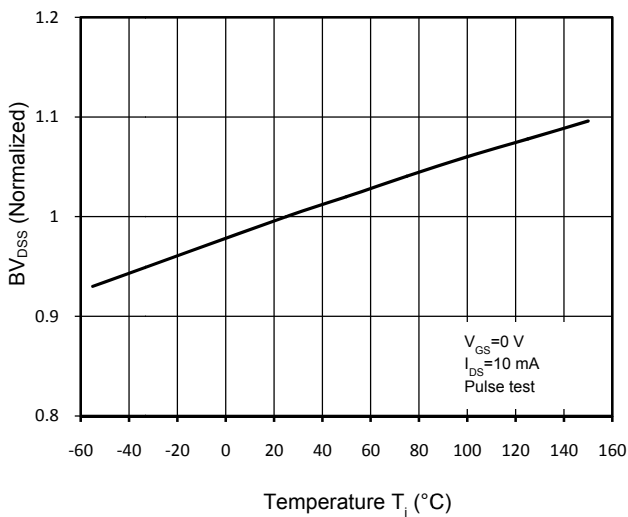


Figure 5. Normalized  $BV_{DS(s)}$  vs. Temperature

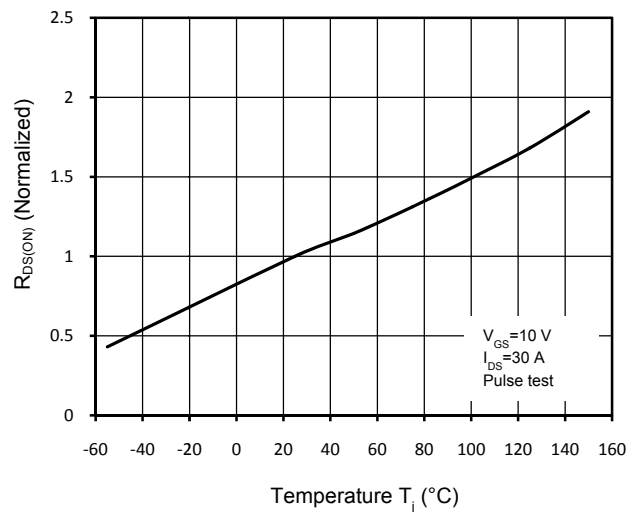


Figure 6. Normalized  $R_{DS(on)}$  vs. Temperature

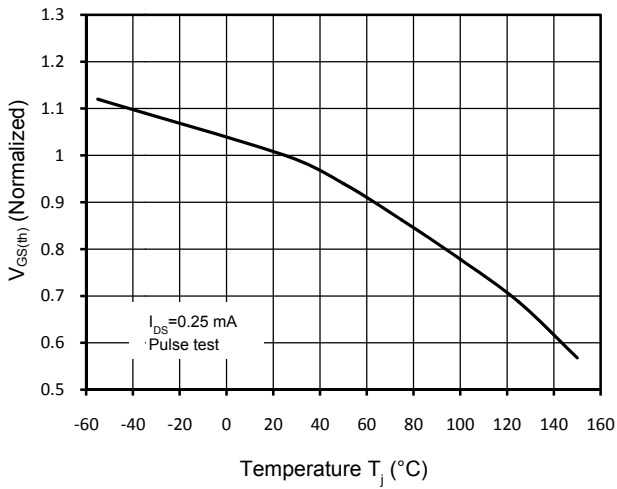


Figure 7. Threshold Voltage vs. Temperature

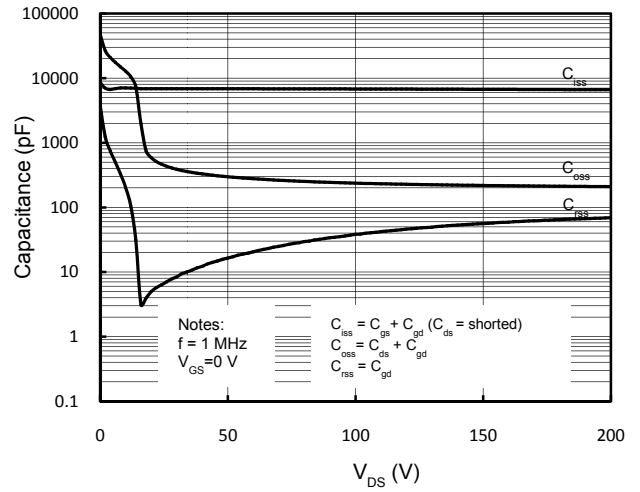


Figure 8. Capacitance Characteristics

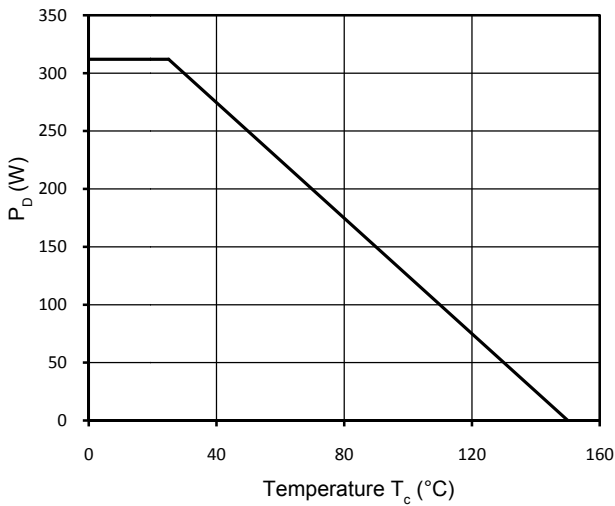


Figure 9. Power Dissipation

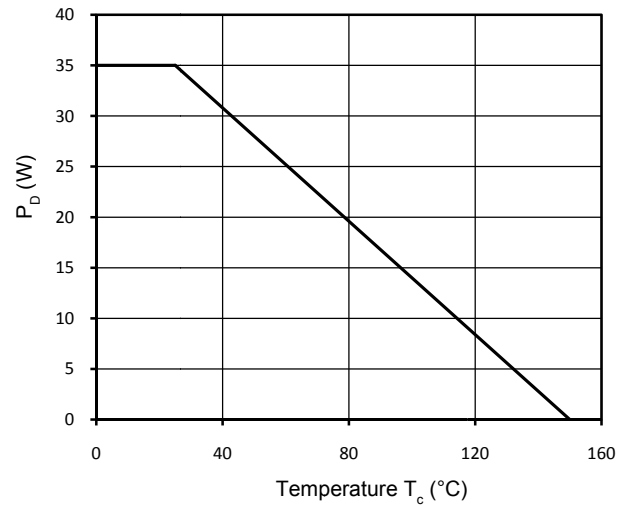


Figure 10. Power Dissipation (TO-220F)

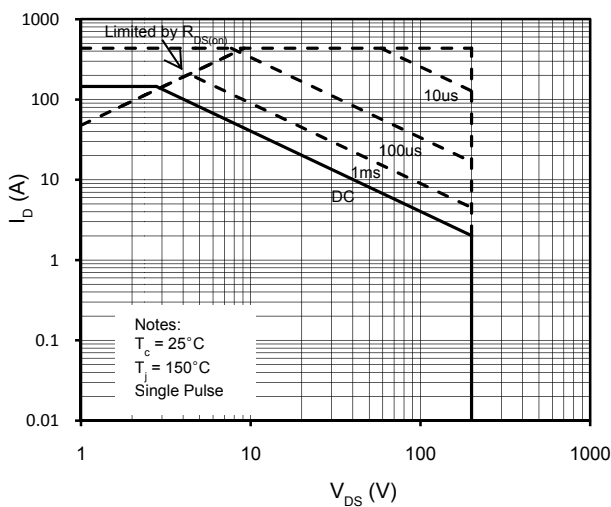


Figure 11. Maximum Safe Operating Area

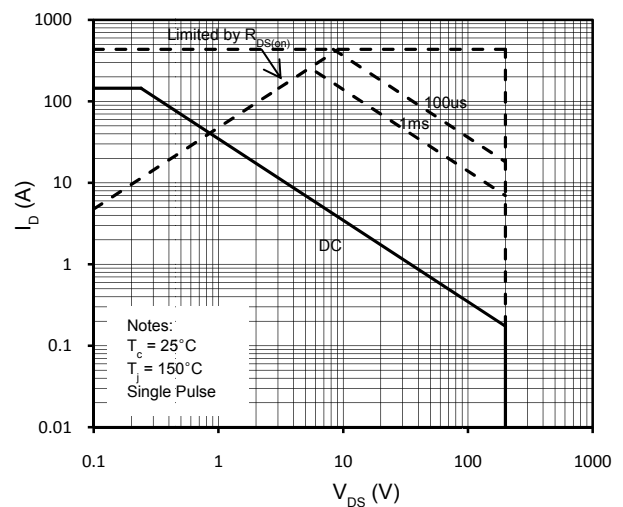


Figure 12. Maximum Safe Operating Area (TO-220F)

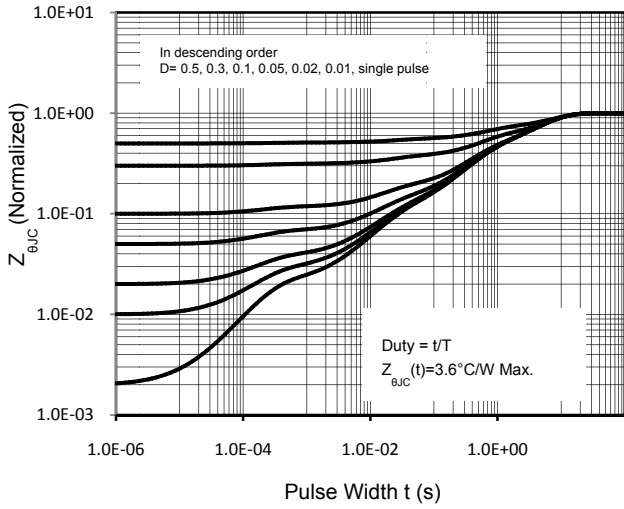


Figure 13. Transient Thermal Response Curve (TO-220F)

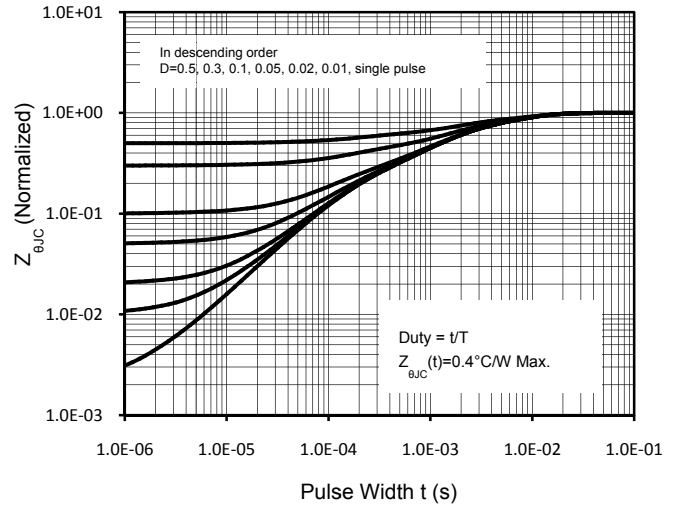


Figure 14. Transient Thermal Response Curve

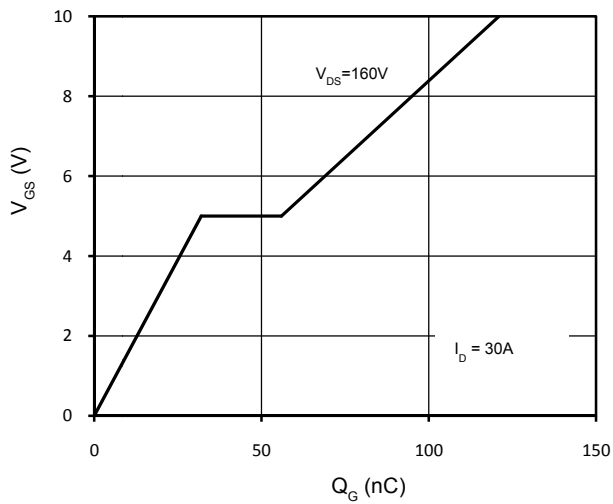


Figure 15. Gate Charge Characteristics

### Gate Charge Test Circuit & Waveform



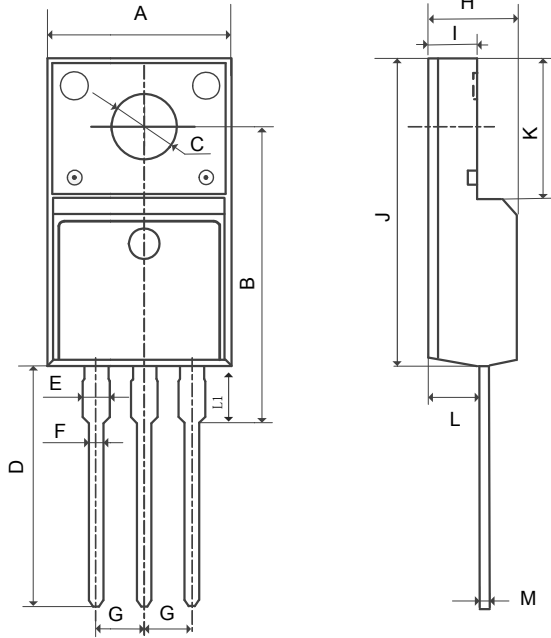
### Switching Test Circuit & Waveforms



### Unclamped Inductive Switching Test Circuit & Waveforms



## Mechanical Dimensions for TO-220F



## COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	9.96	10.36
B	15.10	16.10
C	3.03	3.38
D	12.64	13.28
E	1.18	1.58
F	0.70	0.95
G	2.54REF	
H	4.50	4.90
I	2.34	2.74
J	15.57	16.17
K	6.70REF	
L	2.56	2.96
M	0.40	0.65
L1	2.85	3.45

Mechanical Dimensions for TO-263

COMMON DIMENSIONS



SYMBOL	MM	
	MIN	MAX
A	4.37	4.89
A1	1.17	1.42
A2	2.19	2.89
b	0.70	0.96
b1	1.17	1.47
c	0.30	0.60
D1	8.45	9.35
D4	6.60	—
E	9.80	10.40
E5	7.06	—
e	2.54BSC	
H	14.70	16.00
H2	1.07	1.47
L	2.00	2.70
L1	1.15	1.75
L4	0.25BSC	
θ	0°	9°



## Mechanical Dimensions for TO-262

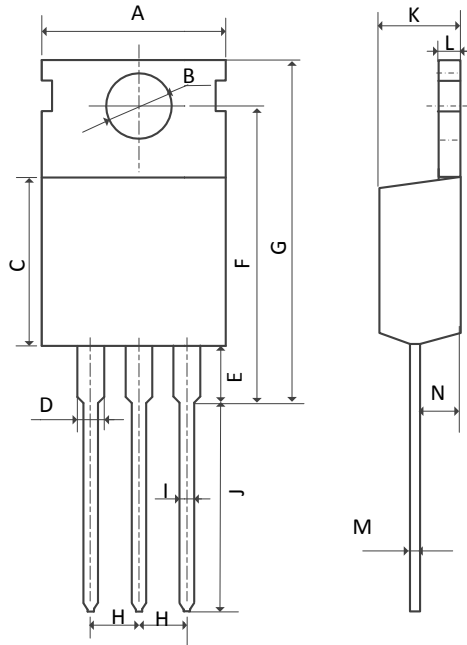
## COMMON DIMENSIONS



SYMBOL	MM	
	MIN	MAX
A	4.37	4.90
A1	1.17	1.42
A2	2.49	2.89
b	0.71	0.96
b2	1.07	1.47
c	0.28	0.53
D	23.20	24.02
D1	8.45	8.90
D2	6.00	—
E1	9.86	10.40
E4	7.06	—
e	2.54BSC	
G	1.25	1.50
H2	—	1.50
L	13.33	14.16
L1	3.50	4.00
L3	1.28	1.58

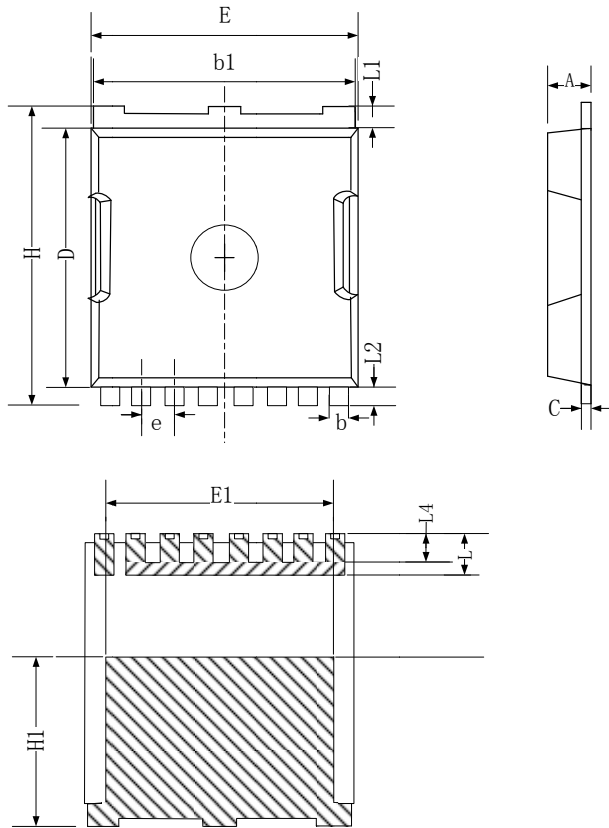
Mechanical Dimensions for TO-220

COMMON DIMENSIONS



SYMBOL	MM	
	MIN	MAX
A	9.70	10.30
B	3.40	3.80
C	8.80	9.40
D	1.17	1.47
E	2.60	3.50
F	15.10	16.90
G	19.60MAX	
H	2.54REF	
I	0.70	0.95
J	9.25	11.00
K	4.30	4.77
L	1.20	1.45
M	0.40	0.65
N	2.20	2.60

**Mechanical Dimensions for TO-LL**

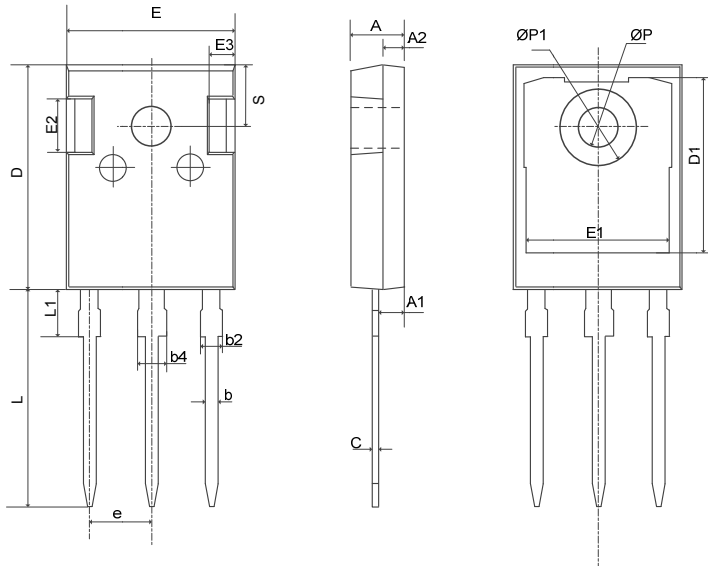


**COMMON DIMENSIONS**

SYMBOL	MM	
	MIN	MAX
A	2.15	2.45
b	0.7	0.95
b <sub>1</sub>	9.6	9.95
C	0.4	0.6
D	10.1	10.6
E	9.6	10.1
E <sub>1</sub>	7.9	8.5
e	1.20BSC	
H	11.38	11.88
H <sub>1</sub>	6.65	7.2
L	1.4	2
L <sub>1</sub>	0.5	0.9
L <sub>2</sub>	0.48	0.72
L <sub>4</sub>	1	1.3

## Mechanical Dimensions for TO-247

## COMMON DIMENSIONS

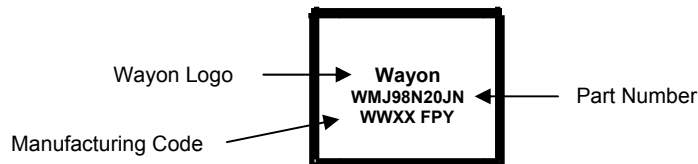


SYMBOL	MM	
	MIN	MAX
A	4.80	5.21
A1	2.21	2.61
A2	1.85	2.16
b	1.07	1.36
b2	1.91	2.41
b4	2.87	3.38
c	0.51	0.75
D	20.70	21.30
D1	16.25	17.65
E	15.50	16.13
E1	12.38	13.60
E2	3.68	5.20
E3	1.00	2.70
e	5.44BSC	
L	19.62	20.32
L1	—	4.40
ØP	3.40	3.80
ØP1	—	7.30
S	6.15BSC	

## Ordering Information

Part	Package	Marking	Packing method
WML98N20JN	TO-220F	WML98N20JN	Tube
WMK98N20JN	TO-220	WMK98N20JN	Tube
WMN98N20JN	TO-262	WMN98N20JN	Tube
WMM98N20JN	TO-263	WMM98N20JN	Tape and Reel
WMLL98N20JN	TO-LL	WMLL98N20JN	Tape and Reel
WMJ98N20JN	TO-247	WMJ98N20JN	Tube

## Marking Information




## Contact Information

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WAYON website: <http://www.way-on.com>

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